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PATENT
2185-0408P

5-17-02

Mullish

THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: Kazumasa HIRAMATSU et al. Conf.: 5987

Appl. No.: 09/522,707 ✓ Group: 2815

Filed: March 10, 2000 ✓ Examiner: BAUMEISTER

For: III-V COMPOUND SEMICONDUCTOR

RECEIVED
MAY 13 2002
TECHNOLOGY CENTER 2800REPLY UNDER 37 C.F.R. § 1.111Assistant Commissioner for Patents
Washington, DC 20231

May 8, 2002

Sir:

In response to the Office Action of November 8, 2001, the period for response having been extended three months, the following amendments and remarks are submitted in connection with the above-identified application.

AMENDMENTSIN THE CLAIMS:

Please amend the claims as follows:

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1. (Amended) A III-V compound semiconductor having a layer formed from a first III-V compound semiconductor expressed by the general formula $\text{In}_u\text{Ga}_v\text{Al}_w\text{N}$ where $0 \leq u \leq 1$, $0 \leq v \leq 1$, $0 \leq w \leq 1$, and $u+v+w=1$, a pattern formed on said layer from a material different not only from said first III-V compound semiconductor but also from a second III-V compound semiconductor hereinafter described, and a layer formed on said first III-V compound